Abstracts

25-42 GHz GaAs Heterojunction Bipolar Transistor Low Phase Noise Push-Push VCOs

D.M. Smith, J.C. Canyon and D.L. Tait. "25-42 GHz GaAs Heterojunction Bipolar Transistor Low Phase Noise Push-Push VCOs." 1989 MTT-S International Microwave Symposium Digest 89.2 (1989 Vol. II [MWSYM]): 725-728.

Two Push-push thin-film VCOs utilizing GaAs/AIGaAs Heterojunction Bipolar Transistors (HBT) that cover the 25 - 42 GHz frequency range are presented. Key features of the designs are: Greater than 33% continuous tuning bandwidth, SSB phase noise less than -70 dBc/Hz at 100 kHz offset, and better than -90 dBc fundamental spur suppression.

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